

MBR3045(F,B,H)CT thru MBR30200(F,B,H)CT

30A Schottky Barrier Rectifier

FEATURE

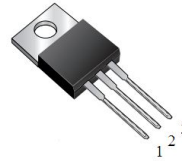
- High current capability
- Low forward voltage drop
- Low power loss, high efficiency
- High surge capability
- High ESD capability
- High temperature soldering guaranteed:
260°C/10s/0.25"(6.35mm) from case

MECHANICAL DATA

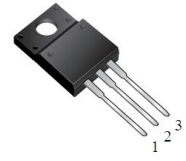
- Case: Molded with UL-94 Class V-0 recognized Flame Retardant Epoxy
- Mounting position: any

TYPICAL APPLICATIONS

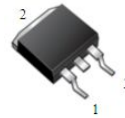
For use in low voltage, high frequency rectifier of switching mode power supplies, freewheeling diodes, DC/DC converters and polarity protection application.



TO-220AB
MBR30XXCT



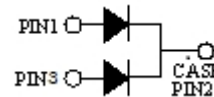
ITO-220AB
MBR30XXFCT



TO-263
MBR30XXBCT



TO-262
MBR30XXHCT



Ratings at 25°C ambient temperature unless otherwise specified, Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

MAXIMUM RATINGS

Parameter	Symbol	MBR3045	MBR3060	MBR30100	MBR30150	MBR30200	units
		CT	CT	CT	CT	CT	
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	45	60	100	150	200	V
Maximum RMS Voltage	V_{RMS}	32	42	70	105	140	V
Maximum DC Blocking Voltage	V_{DC}	45	60	100	150	200	V
Maximum Average Forward Rectified Current at $T_C=90^\circ\text{C}$	total device per diode	$I_{F(AV)}$					A
		30.0					
		15.0					
Peak Forward Surge Current 8.3ms Single Half sine-wave superimposed on rate load per diode (JEDEC method)	I_{FSM}	175					A
Junction Capacitance (Note1)	C_J	800		350			pF
Storage Temperature Range	T_{STG}	-55 to +150					°C
Operation Temperature Range	T_J	-55 to +150					°C

ELECTRONICAL CHARACTERISTICS

Parameter	Symbol	MBR3045	MBR3060	MBR30100	MBR30150	MBR30200	units
		CT	CT	CT	CT	CT	
Maximum Forward Voltage Drop per diode at 15A (Note 2)	V_F	0.60	0.70	0.85	0.90	0.95	V
Maximum DC Reverse Current at rated DC blocking voltage (Note 2)	@ $T_C=25^\circ\text{C}$ @ $T_C=100^\circ\text{C}$	I_R			0.1		mA
		0.15			20.0		

THERMAL CHARACTERISTICS

Parameter	Symbol	ITO-220	TO-220	TO-262 TO-263	units
Typical Thermal Resistance (Note 3)	$R_{th(JC)}$	3.0	2.0	2.0	°C/W

Note:

1. Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc.
2. Pulse test: 300 μs pulse width, 1% duty cycle.
3. Thermal Resistance from Junction to Case Mounted on heatsink.

RATING AND CHARACTERISTIC CURVES (MBR3045(E,B,H)CT THRU MBR30200(E,B,H)CT)

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

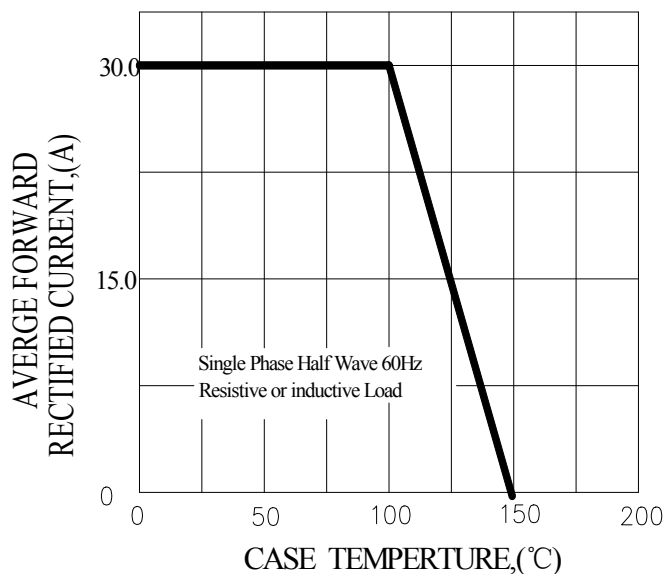


FIG.2-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

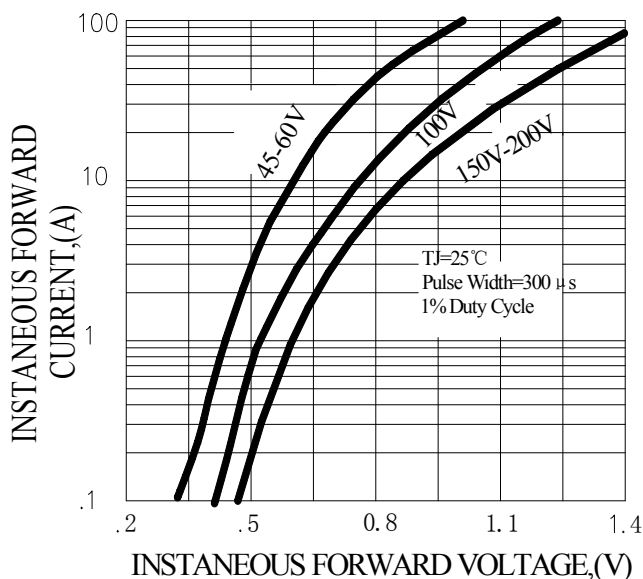


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

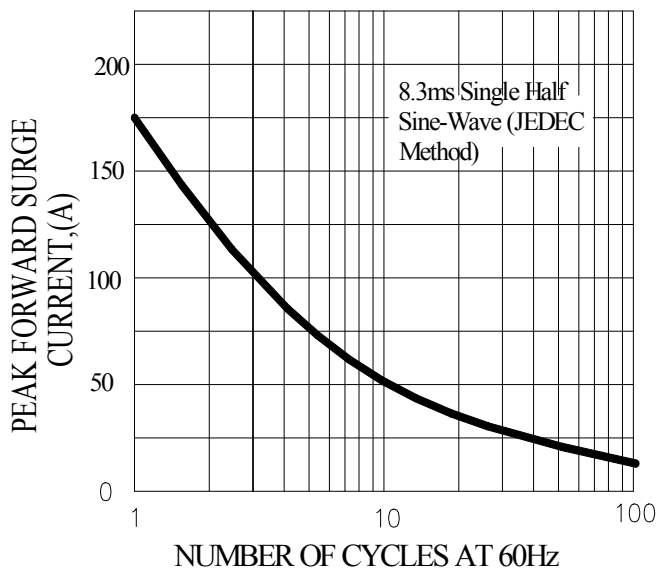
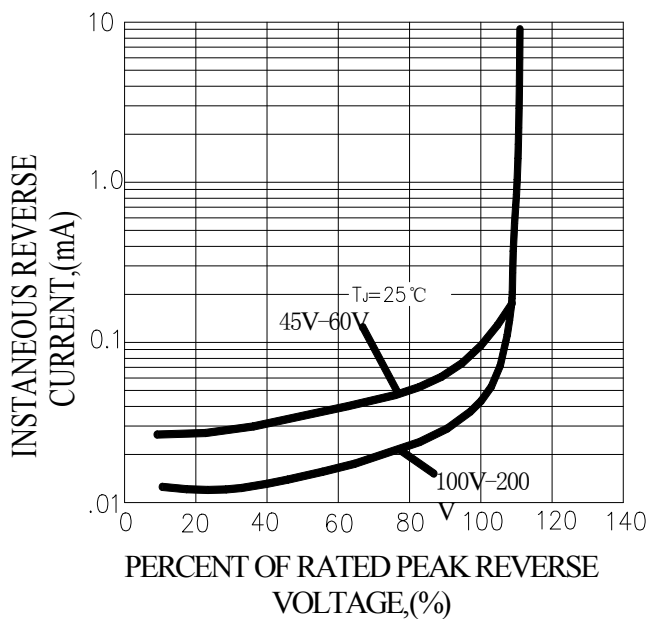


FIG.4-TYPICAL REVERSE CHARACTERISTICS



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Schottky Diodes & Rectifiers](#) category:

Click to view products by [Pingwei](#) manufacturer:

Other Similar products are found below :

[CUS06\(TE85L,Q,M\)](#) [MA4E2039](#) [D1FH3-5063](#) [MBR0530L-TP](#) [MBR10100CT-BP](#) [MBR30H100MFST1G](#) [MMBD301M3T5G](#) [PMAD1103-LF](#) [PMAD1108-LF](#) [RB160M-50TR](#) [RB520S-30](#) [RB551V-30](#) [DD350N18K](#) [DZ435N40K](#) [DZ600N16K](#) [BAS16E6433HTMA1](#) [BAS 3010S-02LRH E6327](#) [BAT 54-02LRH E6327](#) [IDL02G65C5XUMA1](#) [NSR05F40QNXT5G](#) [JANS1N6640](#) [SB07-03C-TB-H](#) [SB1003M3-TL-W](#) [SBAT54CWT1G](#) [SK32A-LTP](#) [SK33A-TP](#) [SK34A-TP](#) [SK34B-TP](#) [SMD1200PL-TP](#) [ACDBN160-HF](#) [SS3003CH-TL-E](#) [STPS30S45CW](#) [PDS3100Q-7](#) [GA01SHT18](#) [CRS10I30A\(TE85L,QM](#) [MA4E2501L-1290](#) [MBR1240MFST1G](#) [MBRB30H30CT-1G](#) [BAS28E6433HTMA1](#) [BAS 70-02L E6327](#) [HSB123JTR-E](#) [JANTX1N5712-1](#) [VS-STPS40L45CW-N3](#) [DD350N12K](#) [SB007-03C-TB-E](#) [SK110-LTP](#) [SK154-TP](#) [SK32A-TP](#) [SK33B-TP](#) [SK35A-TP](#)